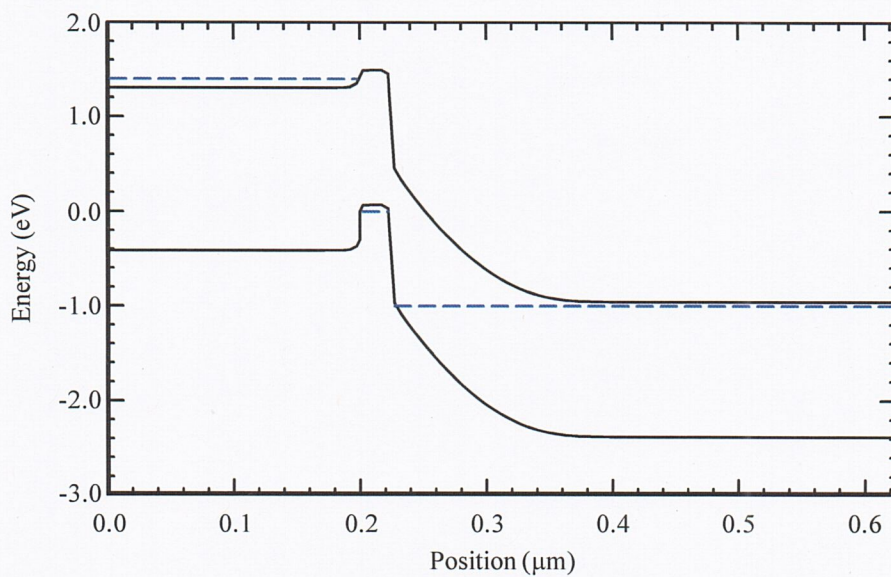


1.



2

$\text{In}_{0.61}$ is a good mole fraction to use because

its electron affinity is the same as for GaAs,

3

i.e., $\Delta E_c = 0$ and, \therefore , the barrier for electron injection into the base is minimized

Q1 = (5)

```
% EECE 480, Assignment 4, 2011
% HBT gain, fTi, fmax
% InGaP/GaAs HBT
%
clear all;
```

```
q=1.6e-19;
kT=8.62e-5*q*300;
Vth=0.0259;
h=4.14e-15*q;
m0=9.1e-31;
eps0=8.85e-12; %F/m
%-----
%Material 1, n-emitter, In_61Ga_39P
%Material 2, p-base, GaAs
%Material 3, n-collector, GaAs
%Only the properties for GaAs are needed in this assignment
```

```
mestar=0.066*m0;
mhstar=0.524*m0;
Eg=1.42*q;
eps=12.9;
```

```
NC=2*(2*pi*mestar*kT/h^2)^(3/2);
NV=2*(2*pi*mhstar*kT/h^2)^(3/2);
ni=sqrt(NC*NV*exp(-Eg/kT));
```

```
vR=sqrt(kT/(2*pi*mestar)); %m/s, use low-doping value
```

```
%vR=2.18e5; 1.25e5;
```

```
%vR=1.25e5; 2.18e5;
```

```
%-----
```

```
NE=5e18*1e6; %m-3
```

```
NB=5e19*1e6;
```

```
NCC=1e17*1e6;
```

```
L=2e-6;
```

```
Z=2e-6;
```

```
WB=25e-9; %m
```

```
VBE=1.4;
```

```
VBC=-1;
```

```
%-----
```

```
mue=(8300.*(1+NB*1e-6./(3.98e15+NB*1e-6./641)).^(-1/3)).*1e-4; %m2/Vs
```

```
De=0.0259.*mue; %m2/s
```

```
taue=(NB*1e-6/1e10+(NB*1e-6)^2/(1.6e29))^(1);
```

```
muh=(380./(1+NB*1e-6.*3.17e-17)).^(0.266))*1e-4; %m^2/Vs
```

```
VbiC=(kT/q)*log(NCC*NB/ni^2);
```

```
WBC=sqrt(2*eps0*eps*(VbiC-VBC)/q*(1/NCC+1/NB));
```

```
%-----IC-----
```

```
n0B=ni^2/NB;
```

```
IC=Z*L*q.*n0B.*(exp(VBE./Vth)-exp(VBC./Vth))./(WB./De+1/vR); %A
```

```
%-----IB-----
```

```
IBrec=Z*L*q.*n0B.*WB./(2.*taue).*((exp(VBE./Vth)-1)+(exp(VBC./Vth)-1))./(1+WB./(4.*vR.*taue)); %A
```

```
IB=IBrec;
```

} Any of these is OK

v_R
 1.1 mA } 1.05e5 m/s
 1.2 " } 1.25e5
 1.5 " } 2.18e5

5.64 μ A } f_{max}
 5.64 " }
 5.64 " }

1

1


```

1 %-----gain-----
beta0=IC/IB
%-----small-sig params-----
2 gm=(L*Z*q*n0B/Vth)*exp(VBE/Vth)/(WB/De+1/vR);
1 CBb=gm*WB/2*(WB/De+1/vR);
Cpi=CBb;
2 Cmu=Z*L*eps*eps0/WBC;
CT=Cpi+Cmu;
2 fTi=gm/(2*pi*CT);
%-----RBsp-----
Bres=1/(q*NB*muh);
RBqnb=Bres*L/(Z*WB);
Rb=RBqnb/12;
fmax=sqrt(fTi/(8*pi*Rb*Cmu));
    
```

200
217
268 } $f(v_R)$

$C_{\pi} f(v_R)$ }
10.6 fF
10.6 "
10.6 "

43.6 nS } $g_m f(v_R)$
47.3 "
58.5 "

532 GHz } $f(v_R)$
578 "
715 "

2.4 fF } $C_B f(v_R)$
2.4 "
2.4 "

77.8 Ω

333 GHz } $f(v_R)$
347 "
386 "

Q2. $I_c = 1$ $I_b = 1$ $\beta = 1$ TOTAL (3)

Q3. $g_m = 2$, $C_{\pi} = 1$, $C_{\mu} = 2$, $f_T = 2$ TOTAL (7)

Q4. $R_b = 3$, $f_{max} = 2$ TOTAL (5)